M icrow ave surface resistance in superconductors with grain boundaries

Y asunori M awatari
E nergy Technology Research Institute,
N ational Institute of Advanced Industrial Science and Technology,
T sukuba, Ibaraki 305{8568, Japan
(D ated: Dec. 28, 2004)

M icrowave—eld distribution, dissipation, and surface impedance are theoretically investigated for superconductors with lam inar grain boundaries (GBs). In the present theory we adopt the two—uid model for intragrain transport current in the grains, and the Josephson—junction model for intergrain tunneling current across GBs. Results show that the surface resistance Rs nonmonotonically depends on the critical current density $J_{\rm cj}$ at GB junctions, and Rs for superconductors with GBs can be smaller than the surface resistance Rs0 for ideal homogeneous superconductors without GBs.

PACS numbers: 7425 Nf, 7420 De, 74.50 + r, 74.81 -g

I. INTRODUCTION

High-tem perature superconductors contain m any grain boundaries (GBs), where the order parameter is locally suppressed due to the short coherence length. GBs have attracted much interest for their basic physics as well as for their applications in superconductors, and play a crucial role in microwave response and surface resistance Rs of high-tem perature superconducting lm s. 5.6.7.8.9.10.11.12.13

E lectrodynam ics of G B junctions can be described using the Josephson-junction model, and one of the most important parameters that characterize GB junctions is the critical current density $\rm J_{cj}$ for Josephson tunneling current across GBs. 14,15,16 The $\rm J_{cj}$ strongly depends on the misorientation angle of GBs. 17,18 In YBa2Cu3O $_7$

 $\mbox{Im}\, s$, J_{cj} can be enhanced 19 and R_s reduced 13 by Ca doping. The investigation of the relationship between R_s and J_{cj} is needed to understand the behavior of R_s and J_{cj} in Ca doped YBa2Cu3O7 $\,$ Im s. The J_{cj} dependence of R_s , however, has not yet been clari ed, and it is not trivial whether GBs enhance the microw ave dissipation that is proportional to R_s .

In this paper, we present theoretical investigation on the microwave eld and dissipation in superconductors with laminar GBs. Theoretical expressions of the surface impedance $Z_s = R_s$ iX $_s$ of superconductors with GBs are derived as functions of J_{cj} at GB junctions.

II. BASIC EQUATIONS

A. Superconductors with grain boundaries

We consider penetration of a microw ave eld (i.e., magnetic induction $B={}_0H$, electric eld E, and current density J) into superconductors that occupy a sem in the area of x>0. We investigate linear response for small microw ave power limit, such that the time dependence of the microw ave eld is expressed by the harm onic factor, $e^{i!t}$, where i!=2 is the microw ave frequency that is much smaller than the energy-gap frequency of

the superconductors. M agnetic induction B is assumed to be less than the lower critical eld, such that no vortices are present in the superconductors. (See Ref. 20 for m icrow ave response of vortices.)

The GBs are modelled to have lam inar structures as in Ref. 21; the lam inar GBs that are parallel to the xz plane are situated at y=m a, where a is the spacing between grains (i.e., e ective grain size) and m=0; 1; 2; ; 1 . The thickness of the barrier of GB junctions, d_j , is much smaller than both a and the London penetration depth , and therefore, we investigate the thin-barrier limit of d_j ! 0, namely, GB barriers situated at m a 0 < y < m a + 0.

B. Two-uid model for intragrain current

We adopt the standard two-uid model 15,16 for current transport in the grain at ma+0 < y < (m+1)a=0. The intragrain current $\rm J=J_s+J_n$ is given by the sum of the supercurrent $\rm J_s=i_sE$ and the normal current $\rm J_n=n_E$, where $\rm _s=1=!_0^2$ and $\rm _n$ is the normal-uid conductivity in the grains. The displacement current $\rm J_d=i!$ E with the dielectric constant can be neglected for a microw averange of !=2 GHz. Ampere's law $\rm _0^1$ r B = (_n+i_s)E is thus reduced to

$$E = i! \frac{2}{g}r \quad B; \qquad (1)$$

where $\ _{g}$ is the intragrain ac eld penetration depth dened by

$$_{q}^{2} = ! _{0}(_{s} i_{n}) = ^{2} i! _{0 n}:$$
 (2)

Combining Eq. (1) with Faraday's law, r E = i!B, we obtain the London equation for magnetic induction $B = B_z(x;y)\hat{z}$ for $y \in m$ a as

$$B_z = {2 \over g} r^2 B_z = 0$$
: (3)

For ideal hom ogeneous superconductors without GBs, Eq. (3) is valid for 1 < y < +1 and the solution is simply given by $B_z(x) = {}_{0}H_{0}e^{x=g}$, and

the electric eld is obtained from Eq. (1) as $E_v(x) =$ i! $_0$ $_q$ H $_0$ e $^{x=}$ g . The surface im pedance Z $_{s0}$ = R $_{s0}$ iX_{s0} for hom ogeneous superconductors is given by Z_{s0} = $E_y(x = 0)=H_0 = i!_0 q$. The surface resistance $R_{s0} = Re(Z_{s0})$ and reactance $X_{s0} = Im(Z_{s0})$ of ideal hom ogeneous superconductors without GBs are given

$$R_{s0} = {}^{2}_{0}!^{2}_{n} = 2;$$
 (4)
 $X_{s0} = {}^{0}_{0}!$ (5)

$$X_{s0} = _{0}!$$
 (5)

1 well below the superconducting transition tem perature T_c .

C. Josephson-junction model for intergrain current

We adopt the Josephson-junction model 4,15,16 for tunneling current across GBs at y = ma. Behavior of the GB junctions is determined by the gauge-invariant phase di erence across GBs, ' $_{i}$ (x), and the voltage induced across GB, V_1 (x), is given by the Josephson's relation,

$$Z_{\text{ma+0}}$$
 $E_y dy = V_j = \frac{0}{2} (\text{i!}'_j);$ (6)

where $_0$ is the ux quantum. The tunneling current parallel to the y axis is given by the sum of the superconducting tunneling current (i.e., Josephson current) $J_{sj} = J_{cj} \sin'_{j}$ and the normal tunneling current (i.e., quasiparticle tunneling current) $J_{nj} = {}_{nj}V_{j}$. The critical current density Jcj at GB junctions is one of the m ost im portant param eters in the present paper, and the resistance-area product of GB junctions corresponds to $1 = n_j$. We neglect the displacement current across GBs, $J_{dj} = i! C_j V_j$ where C_j is the capacitance of the GB junctions.

Here we de ne the Josephson length , and the characteristic current density J_0 as

$$_{J} = (_{0}=4 \quad _{0}J_{cj})^{1=2};$$
 (7)

$$J_0 = {}_{0} = 4 {}_{0} {}^{3}$$
: (8)

The ratio $J_{cj}=J_0=(=_J)^2$ characterizes the coupling strength of GB junctions.²² For weakly coupled GBs, nam ely, $J_{cj} = J_0 = (= _J)^2$ 1 (e.g., high-angle GBs), electrodynamics of the GB junctions can be well described by the weak-link model. For strongly coupled GBs, namely, $J_{cj}=J_0=(=_J)^2>1$ (e.g., low-angle GBs), the Josephson-junction model is still valid but requires appropriate boundary condition at GBs, as given in Eq. (4) in Ref. 22, as pointed out by Gurevich; see also Refs. 21 and 23.

In the sm all-m icrow ave-power lim it such that \sin' , ' $'_{j} = 2 V_{j} = (i!_{0}) \text{ for } j'_{j} = 1, \text{ the } J_{cj} \text{ is reduced to}$

$$J_{sj}' J_{cj}'_{j} = i_{sj}V_{j};$$
 (9)

where $s_j = 2$ $J_{cj}=!$ 0 = 1=2! 0 J . The total tunneling current across GB is thus given by

$$\frac{1}{0} \frac{\partial B_z}{\partial x} = J_{sj} + J_{nj} = (i_{sj} + J_{nj})V_j; \quad (10)$$

Integration of Faraday's law, $@E_y = @x @E_x = @y = i! B_z$, yields

$$E_{x}(x;y = m a + 0) E_{x}(x;y = m a 0)$$

$$= \sum_{m a 0}^{Z_{m a+0}} dy \frac{\partial E_{y}(x;y)}{\partial x} i! B_{z}(x;y) = \frac{\partial V_{j}(x)}{\partial x};(11)$$

where we used Eq. (6). The static version (i.e., !! 0) of Eq. (11) corresponds to Eq. (4) in Ref. 22. Substitution of Eqs. (1) and (10) into Eq. (11) yields the boundary condition for B_z at y = m a,

$$\frac{\text{@B}_{z}}{\text{@y}}_{y=m \text{ a}+0} + \frac{\text{@B}_{z}}{\text{@y}}_{y=m \text{ a} 0} = \frac{a_{j}^{2}}{2} \frac{\text{@}^{2}B_{z}}{\text{@x}^{2}}_{y=m \text{ a}};$$
(12)

where is the characteristic length for ac eld penetration into GBs de ned by

$$_{j}^{2} = ! _{0}a(_{sj} i_{nj})$$
 $= _{0}a(2 J_{cj} = _{0} i! _{nj}):$ (13)

III. SURFACE IM PEDANCE

A. M icrowave eld and surface im pedance

Equations (3) and (12) are combined into a single equation for x > 0 and 1 < y < +1 as

$$B_z$$
 $\frac{2}{g}r^2B_z = a_j^2$ $\frac{x^1}{g^2B_z}$ $\frac{e^2B_z}{e^2x^2}$ (y ma); (14)

whose solution is calculated as

$$\frac{B_{z}(x;y)}{{}_{0}H_{0}} = e^{x=g} + \frac{2}{3} \int_{0}^{Z_{1}} dk \frac{\cosh [K(y = a=2)]}{{}_{g}^{2}K^{2} \sinh (K(a=2))}$$

$$\frac{k \sin kx}{(2K {}_{g}^{2}=a {}_{1}^{2}) + k^{2} \coth (K(a=2))}$$
(15)

for 0 < y < a, where $K = (k^2 + \frac{2}{g})^{1-2}$. The right-hand side of Eq. (14) and the second term of the right-hand side of Eq. (15) re ect the GB e ects. See Appendix A for the derivation of Eq. (15) from Eq. (14).

Electric eld in the grains is obtained from Eq. (1) as $E_y = i! \frac{2}{9} B_z = 0x$, and voltage induced across GB is obtained from Eq.(10) as $V_j = i! a \frac{2}{j} @B_z = @x_{v=0}$. The m ean electric eld E_s at the surface of the superconductor is thus calculated as

$$E_s = \frac{1}{a} \sum_{a=0}^{Z_{a=0}} dy E_y (x = 0;y)$$

Substitution of Eq. (15) into Eq. (16) yields the surface in pedance $Z_s = R_s$ iX_s $E_s = H_0$ as

$$\frac{Z_{s}}{i! _{0 g}} = 1 + \frac{2}{0} \frac{Z_{1}}{0} dk \frac{1}{g^{3}K^{3}}$$

$$\frac{1}{(K_{g}^{2} = \frac{2}{j}) + (k^{2}a = 2) \coth(K_{a} = 2)} : (17)$$

The surface resistance and reactance are given by R $_{\rm S}$ = Re(Z $_{\rm S}$) and X $_{\rm S}$ = Im (Z $_{\rm S}$), respectively.

B. M icrow ave dissipation and surface resistance

The time-averaged electromagnetic energy passing through the surface of a superconductor at x = 0 and 0 < y < a 0 is given by the real part of

$$E = \frac{1}{2_{0}} \int_{0}^{Z_{a0}} dy (E_{y}B_{z})_{x=0} = \frac{a}{2}E_{s}H_{0};$$
 (18)

where $E_s = Z_sH_0$ is de ned by Eq. (16), and $(B_z)_{x=0} = {}_0H_0$. Poynting's theorem ²⁴ states that E is identical to the energy stored and dissipated in the superconductor,

$$E = \frac{1}{2} \sum_{0}^{Z_{1}} dx \int_{0}^{Z_{0}} dy (x_{1} i_{s}) \mathcal{E}^{2}$$

$$+ (x_{1} i_{s}) \mathcal{V}_{1}^{2} \int_{0}^{Z_{0}} dy \frac{i!}{y_{2}} \mathcal{B}_{z}^{2} : (19)$$

The realparts of Eqs. (18) and (19) show that the surface resistance $R_s = Re(E_s = H_0) = Re(Z_s)$ is composed of two terms:

$$R_s = R_{sq} + R_{si}$$
: (20)

The intragrain contribution $R_{\rm sg}$ is from the energy dissipation in the grains, and the intergrain contribution $R_{\rm sj}$ is from the dissipation at GBs:

$$R_{sg} = \frac{1}{a \#_{0} f} \int_{Z_{1}^{0}}^{Z_{1}} dx dy n \#_{f}; \qquad (21)$$

$$R_{sj} = \frac{1}{a H_0 f} dx_{nj} y_j^2;$$
 (22)

Both the intragrain current jJ_g jaround GBs and the intergrain tunneling current jJ_j jacross GBs are suppressed by the GBs, and are increasing functions of J_{cj} . W ith increasing J_{cj} , the intragrain electric eld $\not\equiv j = jJ_g = (_n + i_s)$ jalso increases, whereas the intergrain voltage $\not\!\! J_j = jJ_j = (_{nj} + i_{sj})$ j decreases because

 $_{\rm sj}$ / $J_{\rm cj}.$ The dissipation in the grains, $_{\rm n}$ ½ $\mathring{\rm f}=2$, and the intragrain contribution to the surface resistance, R $_{\rm sg}$, therefore, tend to increase with increasing $J_{\rm cj}$. The dissipation at GBs, $_{\rm nj}\mathring{\rm J}_{\rm j}\mathring{\rm f}=2$, and the intergrain contribution to the surface resistance, R $_{\rm sj}$, on the other hand, decrease with increasing $J_{\rm cj}$.

The surface reactance $X_s = Im(Z_s)$ is also divided into two contributions,

$$X_s = X_{sq} + X_{si}; (23)$$

where the intragrain contribution X $_{\text{sg}}$ and the intergrain contribution X $_{\text{sj}}$ are given by

$$X_{sg} = \frac{1}{a \#_0 f} \int_0^{Z_1} dx dy s \#_f^2 + \frac{!}{0} \#_z^2;$$
(24)

$$X_{sj} = \frac{1}{a H_0 f_0} dx_{sj} V_j f_i$$
 (25)

Both X_{sq} and X_{sj} decrease with increasing J_{cj} .

C. Sim pli ed expressions for surface im pedance

The following Eqs. (26){ (34) show simplified expressions of the surface impedance Z_s , the surface resistance $R_s = Re(Z_s)$, and the surface reactance $X_s = Im(Z_s)$ for certain restricted cases, assuming $_n = _s = 1$ and $_{nj} = _{sj} = 1$ well below the transition temperature.

For small grains of a such that coth (K a=2) '2=K a, Eq. (17) is reduced to

$$Z_s'$$
 i! $_0$ $_q^2 + _j^2$: (26)

The right-hand side of Eq. (14) is reduced to 2_j @ 2 B $_z$ =@ x^2 for a , and the e ective ac penetration depth is given by $_e$ = $(^2_g + ^2_j)^{1=2}$ as in Ref. 21, resulting in the surface in pedance given by Eq. (26). The R $_s$ and X $_s$ for small grains is obtained as

$$\frac{R_s}{R_{s0}}$$
, $1 + \frac{2}{a} \frac{J_0}{J_{cj}}$ $1 + \frac{4^2_{nj}}{a_n} \frac{J_0}{J_{cj}}$; (27)

$$\frac{X_s}{X_{s0}}$$
, $1 + \frac{2}{a} \frac{J_0}{J_{cj}}$; (28)

where R_{s0} , X_{s0} , and J_0 are de ned by Eqs. (4), (5) and (8), respectively. Equation (27) is decomposed into the intragrain R_{sg} and intergrain R_{sj} contributions, as $R_{sg} = R_{s0}$ ' $(1 + 2 \ J_0 = aJ_{cj})^{1=2}$ and $R_{sj} = R_{sg}$ ' $(4^2 \ n_j = a_n) (J_0 = J_{cj})^2$, respectively.

Equation (26) is further simplified when a $2 \frac{2}{J}$ = for small grain and weakly coupled GBs as

$$Z_{s}'$$
 i! _{0 j}; (29)

and we have

$$\frac{R_{s}}{R_{s0}} , \frac{2_{nj}}{n} \frac{2}{a} \frac{1=2}{J_{cj}} \frac{J_{0}}{J_{cj}} \stackrel{3=2}{;} (30)$$

$$\frac{X_{s}}{X_{s0}} , \frac{2}{a} \frac{1=2}{J_{cj}} \frac{J_{0}}{J_{cj}} : (31)$$

$$\frac{X_s}{X_{s0}}$$
, $\frac{2}{a}$ $\frac{J_0}{J_{cj}}$: (31)

Thus, we obtain the dependence of R $_{\rm S}$ and X $_{\rm S}$ on the m aterial param eters as R $_{\rm s}$ / $_{\rm n\,j}a$ $^{1=2}$ J $_{\rm c\,i}^{3=2}$ and X $_{\rm s}$ / a $^{1=2}$ J $_{ci}^{1=2}$, which are independent of . The R $_{s}$ given by Eq. (30) for the small grain and weakly coupled GBs is mostly caused by intergrain dissipation, Rs ' Rsi R_{sq} . For X_s given by Eq. (31), on the other hand, both intragrain X_{sq} and intergrain X_{sj} contribute to the total $X_s = X_{sg} + X_{sj}$.

For large J_{cj} (i.e., strong-coupling lim it) such that K $_{q}^{2}=\frac{2}{1}$ ($k^{2}a=2$) coth (K a=2), Eq. (17) for the surface im pedance Z_s is simplied as

$$Z_s'$$
 i! $_0$ $_q + _i^2 = 2_q$; (32)

and we have

$$\frac{R_s}{R_{s0}}$$
, $1 = \frac{J_0}{a J_{cj}} + \frac{4^2 nj}{a n} = \frac{J_0}{J_{cj}}^2$; (33)

$$\frac{X_s}{X_{s0}}$$
 ' 1 + $\frac{J_0}{aJ_{cj}}$: (34)

The rst and second terms of the right-hand side of Eq. (33) correspond to the intragrain contribution, R_{sq} , whereas the third term corresponds to the intergrain contribution, Rsi.

IV. DISCUSSION

Figure 1(a) and (b) shows J_{cj} dependence of R_s . As shown in Fig. 1(a), the intergrain contribution Rsi is dom inant for weakly coupled GBs (i.e., small $J_{ci}=J_0$ regim e), whereas the intragrain contribution R $_{\rm sg}$ is dom inant for strongly coupled GBs (i.e., large $J_{cj}=J_0$). The R_{sj} decreases with increasing J_{cj} as R_{sj} / $J_{cj}^{1:5}$ [see Eq. (30)], whereas R $_{\text{sg}}$ increases with J_{cj} . The resulting surface resistance $R_s = R_{sj} + R_{sq}$ nonmonotonically depends on J_{ci} and has a minimum, because R_s is determ ined by the competition between R $_{
m sj}$ and R $_{
m sg}$. As shown in Fig. 1 (c), on the other hand, X $_{\rm s}$ m onotonically decreases with increasing J_{cj} [i.e., X_s / $J_{cj}^{0:5}$ for weakly coupled GBs as in Eq. (31)].

The nonmonotonic dependence of R_s on the grain size a is also seen in Fig.1(b). For small $J_{\text{cj}}\!=\!\!J_0$ the R $_s$ decreases with increasing a as R_s / a 0.5° [see Eq. (30)], whereas R_s increases with a for large $J_{ci}=J_0$.

The R_s for strongly coupled GBs can be smaller than R_{s0} for idealhom ogeneous superconductors without GBs, namely, R $_{\rm s}$ =R $_{\rm s0}$ < 1 for J $_{\rm cj}$ =J $_{\rm 0}$ > 1. The m in im um surface resistance for $n_j = n = 0.2$ is $R_s = R_{s0}$

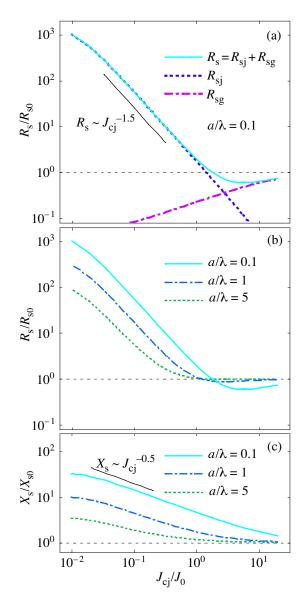


FIG. 1: Dependence of surface resistance $R_s = Re(Z_s)$ and surface reactance $X_s = Im (Z_s)$ [i.e., Eq. (17) with Eqs. (2) and (13)] on critical current density J_{cj} at GB junctions. R $_{\text{S}}$ is normalized to the surface resistance without GB, i.e., R so given by Eq. (4), X_s is normalized to X_{s0} given by Eq. (5), and J_{cj} is normalized to J_0 dened as Eq. (8). Param eters are !=2 = 10 G H z, = 0.2 m, $_{\rm n}$ = 10 7 1 m 1 , and $_{\rm n\,j}$ = 10^{13} 1 m 2 , which yield R $_{\rm s\,0}$ = 0.25 m , X $_{\rm s\,0}$ = 16 m , and $J_0 = 1:6 \quad 10^{10} \, \text{A/m}^2$. (a) Total surface resistance $R_s =$ $R_{sj} + R_{sg}$, intergrain contribution R_{sj} given by Eq. (22), and intragrain contribution R_{sg} given by Eq. (21) for a==0:1. (b) R_s and (c) X_s for a = 0:1, 1, and 5.

 $a = 5, R_s = R_{s0}$ $0.86 \text{ for a} = 1, \text{ and } R_s = R_{s0}$ for a = 0.1. The m in im um $R_s = R_{s0}$ is further reduced when n = n is further reduced.

Theoretical results shown above may possibly be observed by measuring R_s , X_s , and J_{cj} in Ca doped $YBa_2Cu_3O_7$ Im s. The enhancement of J_{ci} (Ref. 19) and reduction of Rs (Ref. 13) by Ca doping are individually observed in YBa $_2$ Cu $_3$ O $_7$, but simultaneous measurem ents of J $_{cj}$ and R $_s$ are needed to investigate the relationship between R $_s$ and J $_{cj}$. The nonmonotonic J $_{cj}$ dependence of R $_s$ for strongly coupled GBs m ay be observed in high quality lms with small grains a < and with large J $_{cj}$ on the order of J $_0$ 16^{10} A=m 2 at low tem peratures.

V. CONCLUSION

We have theoretically investigated the microwave—eld distribution in superconductors with laminar GBs. The eld calculation is based on the two—uid model for current transport in the grains and on the Josephson—junction model for tunneling current across GBs. Results show that the microwave dissipation at GBs is dominant for weakly coupled GBs of $J_{\rm cj}$ J_0 , whereas dissipation in the grains is dominant for strongly coupled GBs of $J_{\rm cj}$ J_0 . The surface resistance $R_{\rm s}$ nonmonotonically depends on $J_{\rm cj}$; the $R_{\rm s}$ decreases with increasing $J_{\rm cj}$ as $R_{\rm s}$ / $J_{\rm cj}^{1:5}$ for $J_{\rm cj}$ J_0 , whereas $R_{\rm s}$ increases with $J_{\rm cj}$ for $J_{\rm cj}$ for $J_{\rm cj}$ as $R_{\rm s}$ and the surface resistance of superconductors with GBs can be smaller than that of ideal hom ogeneous superconductors without GBs.

A cknow ledgm ents

I gratefully acknow ledge H . O bara, $J\mathcal{L}$. N ie, A . Sawa, M . M urugesan, H . Y am asaki, and S . K osaka for stimulating discussions.

APPENDIX A

Equation (15) is derived by solving Eq. (14) with the boundary condition of B $_{\rm Z}$ = $_{\rm 0}$ H $_{\rm 0}$ at x = 0, as follows.

W e introduce the Fourier transform of B $_{\rm z}$ (x;y) and

 $B_z(x; m a) = B_z(x; 0)$ as

respectively. The Fourier transform of Eq. (14) leads to

$$\frac{\tilde{b}(k;q)}{_{0}H_{0}} = 2 \quad (q)\frac{k}{K^{2}} + \frac{k}{K^{2} + q^{2}} \quad e^{im \, qa} \quad 1 \quad \frac{k\tilde{b}_{0}(k)}{_{0}H_{0}} \quad ;(A.3)$$

where $K = (k^2 + {g \choose g})^{1=2}$ and $= a {g \choose j} = {g \choose g}$. Substituting Eq. (A3) into Eq. (A2), we have

$$\frac{E_0(k)}{_0H_0} = \frac{k}{K^2} + k^{-1} \frac{kE_0(k)}{_0H_0}^{\#} X^{-Z_{+1}} \frac{dq}{2} \frac{e^{im \cdot qa}}{K^2 + q^2};$$
(A 4)

which is reduced to

$$\frac{B_0(k)}{_0H_0} = \frac{1}{k} \frac{2}{_{KK}_{g}^2} \frac{1}{_{2K} + k^2 \coth(K a=2)} : \quad (A.5)$$

 $B_z(x;y)$ is calculated from $\tilde{b}(k;q)$ given by Eq. (A3) as

$$\frac{B_{z}(x;y)}{{}_{0}H_{0}} = \frac{2^{Z_{1}}}{{}_{0}} dk \frac{Z_{1}}{{}_{0}H_{0}} \frac{Z_{1}}{{}_{0}H_{0}} \frac{E(k;q)}{{}_{0}H_{0}} e^{iqy} \sin kx$$

$$= e^{x=g} + \frac{2^{Z_{1}}}{{}_{0}} dk k \sin kx 1 \frac{kE_{0}(k)}{{}_{0}H_{0}}$$

$$\frac{X^{Z_{1}+1}}{{}_{0}} \frac{dq}{2} \frac{e^{iq(y m a)}}{K^{Z_{1}+q^{2}}} : (A 6)$$

Substitution of Eq. (A5) into Eq. (A6) yields Eq. (15).

G.Deutscher and K.A.Muller, Phys. Rev. Lett. 59, 1745 (1987).

² J.M annhart and H.H ilgenkam p, Physica C 317-318, 383 (1999).

³ D. Larbalestier, A. Gurevich, D.M. Feldmann, and A. Polyanskii, Nature 414, 368 (2001).

⁴ H.Hilgenkam p and J.M annhart, Rev.M od.Phys.74,485 (2002).

T L. Hylton, A. Kapitulnik, M R. Beasley, JP. Carini, L. Drabeck, and G. Gruner, Appl. Phys. Lett. 53, 1343 (1988)

⁶ C. Attanasio, L. Maritato, and R. Vaglio, Phys. Rev. B 43, 6128 (1991).

⁷ J. Halbritter, J. Appl. Phys. 71, 339 (1992).

 $^{^{8}}$ P.P.Nguyen, D.E.O ates, G.D resselhaus, and M.S.D res-

selhaus, Phys. Rev. B 48, 6400 (1993).

⁹ R. Fagerberg, and J.K. Grepstad, J. Appl. Phys. 75, 7408 (1994).

¹⁰ M .M ahel, Solid State Commun. 97, 209 (1996).

J. M cD onald and JR. Clem, Phys. Rev. B 56, 14 723 (1997).

J.C. Gallop, A. Cowie, and L.F. Cohen, Physica C 282– 287, 1577 (1997).

H. Obara, A. Sawa, H. Yam asaki, and S. Kosaka, Appl. Phys. Lett. 78, 646 (2001).

¹⁴ A.Barone and G.Paterno, Physics and Applications of the Josephson E ect (Wiley, New York, 1982).

 $^{^{15}}$ M . T inkham , Introduction to Superconductivity, 2nd ed. (M cG raw \pm ill, N ew Y ork, 1996).

 $^{^{16}}$ T. Van Duzer and C.W. Turner, Principles of Supercon-

- ductive D evices and C incuits, 2nd ed. (P rentice H all, N ew Jersey, 1999).
- D.D im os, P.Chaudhari, J.M annhart, and F.K. LeG oues, Phys. Rev. Lett. 61, 219 (1988); D.D im os, P.Chaudhari, and J.M annhart, Phys. Rev. B 41, 4038 (1990).
- A. Gurevich and E. A. Pashitskii, Phys. Rev. B 57, 13878 (1998).
- A. Schmehl, B. Goetz, R. R. Schulz, C. W. Schneider, H. Bielefeldt, H. Hilgenkamp, and J. Mannhart, Europhys. Lett. 47, 110 (1999); C. W. Schneider, R. R. Schulz, B. Goetz, A. Schmehl, H. Bielefeldt, H. Hilgenkamp, and J. Mannhart, Appl. Phys. Lett. 75, 850 (1999); G. Hammerl, A. Schmehl, R. R. Schulz, B. Goetz, H. Bielefeldt, C. W. Schneider, H. Hilgenkamp, and J. Mannhart, Nature (Lon-
- don) 407, 162 (2000).
- ²⁰ M W . Co ey and JR. Clem, Phys. Rev. Lett. 67, 386 (1991); E H. Brandt, ibid. 67, 2219 (1991).
- ²¹ T L. Hylton and M R. Beasley, Phys. Rev. B 39, 9042 (1989).
- ²² A.Gurevich, Phys. Rev. B 46, R3187 (1992).
- Yu M. Ivanchenko and T.K. Soboleva, Phys. Lett. A 147, 65 (1990); R.G. M. ints and I.B. Snapiro, Phys. Rev. B 51, 3054 (1995); V.G. Kogan, V.V. Dobrovitski, J.R. Clem, Y. M. awatari, and R.G. M. ints, Phys. Rev. B 63, 144501 (2001).
- J.D. Jackson, Classical Electrodynamics (Wiley, New York, 1975).